

In-situ determination of the energy dependence of the high frequency mobility in polymers

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The high-frequency mobility (μ_{hf}) in disordered systems is governed by transport properties on mesoscopic length scales, which makes it a sensitive probe for the amount of local order. Here we present a method to measure the energy dependence of μ_{hf} by combining an electrochemically gated transistor with in-situ quasi-optical measurements in the sub-terahertz domain. We apply this method to poly([2-methoxy-5-(3',7'-dimethyloxy)]-*p*-phenylene vinylene) (OC₁C₁₀-PPV) and find a mobility at least as high as $0.1 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$.

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In many materials of practical interest, like doped or amorphous semiconductors, metal-insulator composites, and doped conjugated polymers, disorder introduces charge localization, and hence charge transport is due to hopping of the carriers instead of band conduction. Because of the disorder the mobility is often low. For example, in polymeric light emitting diodes the dc hole mobility (μ_{dc}) for the often used conjugated polymer poly([2-methoxy-5-(3',7'-dimethyloxy)]-*p*-phenylene vinylene) (OC₁C₁₀-PPV) is typically of the order of $10^{-11} \text{ m}^2/\text{Vs}$ at room temperature. (1; 2; 3; 4; 5) Because μ_{dc} in a disordered system is limited by the weakest link in the conduction path, it usually can not provide detailed insight in the transport processes involved on mesoscopic length scales. As previously demonstrated for metal-insulator composites, chemically doped polymers and polymers in solution, measurements of μ as function of frequency are more informative for the mesoscopic structure and the conduction process. (6; 7; 8) For example, a few years ago Hoofman *et al.* applied their time-resolved microwave conductivity technique to investigate the charge mobility in a PPV solution. (7) In this method a high energy electron beam (3 MeV) creates doping ions, and the differences in transmission for 30 GHz radiation is translated to the mobility, which was found to be about $2 \cdot 10^{-5} \text{ m}^2/\text{Vs}$. Martens *et al.* used voltage-modulated millimeter-wave spectroscopy to determine the carrier mobility in solid state devices of OC₁C₁₀-PPV at frequencies between 10 and 200 GHz. (8) The carriers were introduced from contacts in the device

by a large electric field of around hundred V/ μm and the high frequency mobility μ_{hf} , deduced from the attenuation of the sub-THz radiation through the device, was shown to be as high as $10^{-4} \text{ m}^2/\text{Vs}$. The dependence of μ_{hf} on the applied voltage over the contacts was linked to the occupation of the levels in the (almost Gaussian) density of states (DOS) (9). This finding was very recently supported by DOS data obtained with an electrochemically gated transistor (EGT). (10; 11) The method was proven to be reliable for PPV and the mobility could be followed over a relatively large energy scan of more than an eV. (11; 12)

In this letter we describe a method to measure the high-frequency mobility, which combines the process of electrochemical doping using an EGT with in-situ quasi-optical measurements in the sub-terahertz domain. (10; 11) Knowing the amount of doping and the precise energy calibration are great advantages over the time-resolved microwave conductivity or voltage-modulated millimeter-wave spectroscopy methods. Using OC₁C₁₀-PPV as an illustration, we determine the dependence of the high-frequency mobility on the electrochemical potential.

A major problem to overcome when working with ionic solutions is that ions in the electrolyte strongly absorb at sub-THz frequencies. In earlier studies with similar electrolytes and the polymer dissolved in the solution, the absorption by the electrolyte completely dominated and prevented investigation of the properties of the polymer films. (13) To overcome this difficulty, the electrochemical cell was designed to minimize the path of the radiation in the solution. In our experiments the radiation frequencies are around 190 GHz. The cell has been made out of quartz and had a free space of 2.5 mm in the direction the radiation propagates. Still, when filled with electrolyte it absorbs more than 100 dB, which makes the measurements impossible. To minimize the absorp-

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tion of the electrolyte, a 1 mm teflon or quartz spacer (for both materials the absorption is very low) was mounted behind the 0.5 mm thick sample (glass plus film), see Fig. 1. By this procedure the transmission loss could be kept to an acceptable level. For the undoped sample at 190 GHz the suppression of the transmission was found to be of the order of 50 dB.

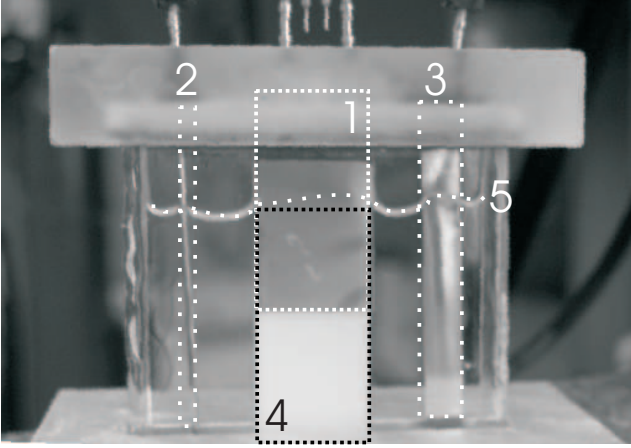


FIG. 1 Front view of the electrochemical cell used. The regions indicated by dotted lines are: 1 - sample (PPV on a glass substrate), 2 - Ag reference, 3 - Pt counter electrode, 4 - Teflon spacer positioned behind the sample, and 5 - level of the electrolyte in the cell. The cell dimensions are about 5 cm $\times$ 5 cm. A cap with a rubber O-ring seals the cell. Four feed-through connections in the cap enable electrical contact with the reference and counter electrodes and the source and drain contacts on the sample. The direction in which radiation propagates is perpendicular to the plane of the figure.

In the EGT cell a counter electrode (Pt foil) and a reference electrode (Ag wire) are required, see Fig. 1, for calibrated changes in the electrochemical potential. Because PPV is air-sensitive, the cell has to be air-tight. Casting of the samples on ITO covered glass and mounting in the cell were done under nitrogen atmosphere.

The measuring procedure is straightforward: the electrochemical cell is placed between the source and detection horns of the sub-THz setup and by creating a potential difference (ΔV) between the working electrode (ITO) and the reference electrode (Ag) doping is achieved. Results of a typical measurement, where the transmission is monitored as function of time, are shown in Fig. 2a. To get a measurable difference in transmission between the undoped and doped OC₁C₁₀-PPV sample, the thickness of the PPV layer had to be more than 10 micron. Initially ΔV is zero, that means no doping. After about 200 seconds ΔV is changed to a value of 1 V. Once the steady-state value in transmission is achieved ($\sim 10^3$ seconds after the potential change) ΔV is set to 0 V, corresponding again to an undoped sample. While doping, we observe that the transmission decreases by 6-7 dB and on switching back to a non-doped state (0 V) the original transmission value is recovered. Repeating this proce-

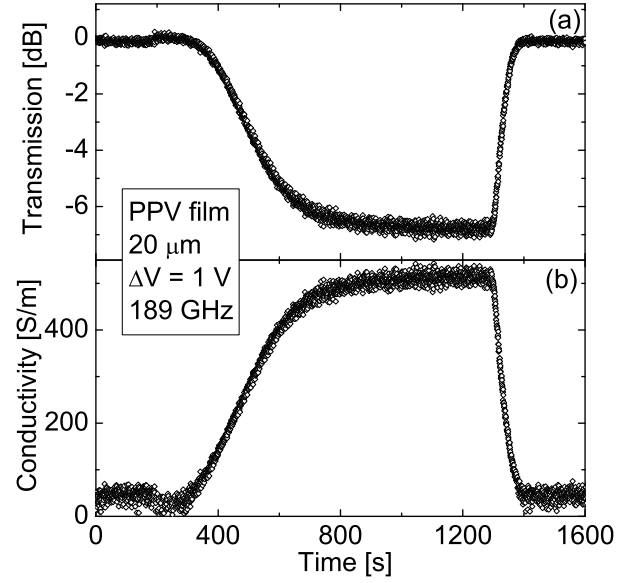


FIG. 2 Upper panel: relative transmission of sub-THz radiation measured as a function of time for a 20 μ m thick PPV sample. At $t=0$ the measurement is started with no potential difference between the ITO electrode and the quasi-reference Ag electrode, and the transmission here is chosen as 0 dB. After about 200 s the potential on the ITO is raised suddenly while the transmission is monitored continuously. Once the steady transmission value is reached the difference in potential is brought back to 0 V and the original value in transmission (corresponding to the undoped sample) is recovered. Bottom panel: conductivity calculated from the measured transmission via Eqn. 1.

dure several times we obtained the transmission changes corresponding to different values of the applied potential on the working electrode. From the measured transmission the conductivity σ can be calculated via

$$|T| = \frac{A}{1 + [(d/2c\epsilon_0)\sigma(\omega)]^2}, \quad (1)$$

with A a constant that takes into account the transmission of the substrate, electrolyte, cell's walls, etc., d is the polymer film thickness, c the speed of light, ϵ_0 the permittivity of free space and $\sigma(\omega)$ the film conductivity. Eqn. 1 is only valid, if the optical thickness of the film is less than the wavelength of the probing radiation, which is satisfied in our case for films with thickness less than 25 μ m. The calculated conductivity as function of time is shown in Fig. 2b.

The measured conductivities for different potentials, see Fig. 3a, compare well with those of organic crystals or amorphous silicon, with typical values of the order of 300 S/m. From the conductivity, the high frequency mobility can be extracted if we know the number of participating carriers. This number depends on the density of states and the electrochemical potential. In dc-transport, which is an interchain and intrachain process, due to the Fermi-Dirac statistics especially transitions in

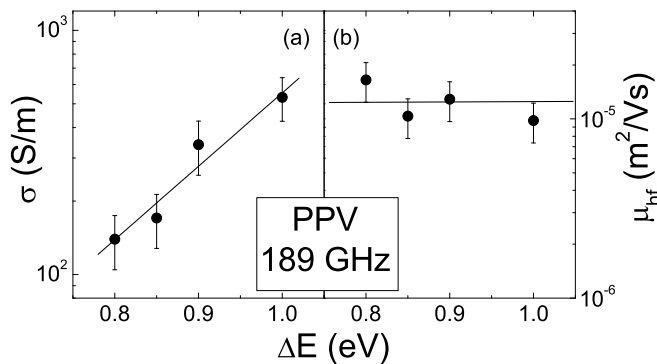


FIG. 3 (a) The conductivity vs. energy. The energy is relative to the Ag pseudo-reference, which is 4.47 V below the vacuum level (the level of 1 eV is at -5.47 eV below the vacuum level). (b) The mobility determined from the conductivity data of the left panel, assuming a homogeneous loading of the film and all doped charges to participate. The data are for PPV at 189 GHz; lines are guides to the eye.

a band of $k_B T$ around the chemical potential contribute to the conductivity.(11) Close to a THz, most charges oscillate within a segment of the chain, and the number of contributing charges will be higher (for polypyrrole only in the mid-infrared response all charges participate (14)). The number of all doped charges is obtained by integrating the density of states known from previous experiments on thin PPV-devices,(11) and will be used here for estimating (the lower limit) of μ_{hf} . When the electrochemical potential with respect to the Ag reference equals 0.8 eV, the mobility is slightly higher than 10^{-5} m^2/Vs . A similar value is deduced at half band filling (at an electrochemical potential of 1 eV (11)). These results reproduce the findings of Hoofman *et al.* within a factor two,(7) which shows that at low doping the frequency dependence of μ_{hf} between 30 GHz and 200 GHz is negligible. Qualitatively these findings confirm the ultra-fast oscillatory motion of the carriers in the chain segment. As a comparison, the mobilities obtained in the best organic crystals are around 10^{-3} m^2/Vs , (15; 16) i.e. two orders of magnitude higher than reported here for low doping levels.

In samples of 0.2 μm the typical time constant for the transmission change was of the order of 0.2 s or at least a factor of 10^3 shorter than the 200 - 600 s for the 20 μm film, see Fig. 2. Differences of that order of magnitude are expected in diffusion processes, where time goes with the mean distance squared; a real computation would have to account for the opening of the diffusion channels (swelling) and the history of the experiment.

In conclusion, we have developed a method to measure the high frequency mobility based on an electrochemically gated transistor. The advantages over the existing methods are its ability to deal with solid state films, higher doping levels than the ones obtained in diode configurations, and the precise energy and concentration calibration. The results show that the structure at short length scales supports a mobility which comes close to those of organic crystals.

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